

# $\mu$ PA2670T1R

DUAL P-CHANNEL MOSFET -20 V, -3.0 A,  $79 \text{ m}\Omega$ 

R07DS0833EJ0101 Rev.1.01 Apr 15, 2013

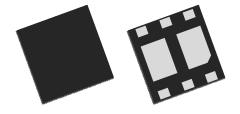
### **Description**

The  $\mu$ PA2670T1R is Dual P-channel MOS Field Effect Transistors for switching application.

This device features a low on-state resistance and excellent switching characteristics, and is suitable for applications such as power switch of portable machine and so on.

### **Features**

- -1.8V drive available
- Low on-state resistance
  - --- R<sub>DS (on)1</sub> = 79 mΩ MAX. (V<sub>GS</sub> = -4.5 V, I<sub>D</sub> = -1.5 A)
  - $R_{DS (on)2} = 105 \text{ m}\Omega \text{ MAX}.$  ( $V_{GS} = -2.5 \text{ V}, I_D = -1.5 \text{ A}$ )
  - --- R<sub>DS (on)3</sub> = 182 mΩ MAX. (V<sub>GS</sub> = -1.8 V, I<sub>D</sub> = -1.5 A)
- Built-in gate protection diode
- Lead-free and Halogen-free



6pinHUSON2020(Dual)

# **Ordering Information**

Part Number	Package
μPA2670T1R-E2-AX* <sup>1</sup>	6pinHUSON2020

Note: \*1.Pb-free (This product does not contain Pb in the external electrode and other parts.)

### Absolute Maximum Ratings ( $T_A = 25$ °C)

Item	Symbol	Ratings	Unit
Drain to Source Voltage (V <sub>GS</sub> = 0 V)	$V_{DSS}$	-20	V
Gate to Source Voltage (V <sub>DS</sub> = 0 V)	$V_{GSS}$	∓10	V
Drain Current (DC)	I <sub>D(DC)</sub>	∓3.0	Α
Drain Current (pulse) *1	I <sub>D(pulse)</sub>	∓12	Α
Total Power Dissipation (1 unit, 5 s) *2	P <sub>T1</sub>	1.5	W
Total Power Dissipation (2 units, 5 s) *2	P <sub>T2</sub>	2.3	W
Channel Temperature	T <sub>ch</sub>	150	°C
Storage Temperature	T <sub>STG</sub>	-55 to +150	°C

Notes: \*1. PW≤10 μs, Duty Cycle≤1%

\*2. Mounted on glass epoxy board of 25.4mm x 25.4mm x 0.8mmt

# Electrical Characteristics (T<sub>A</sub> = 25°C)

Characteristics	Symbol	MIN.	TYP.	MAX.	Unit	Test Conditions	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>			-1.0	μA	V <sub>DS</sub> = -20 V, V <sub>GS</sub> = 0 V	
Gate Leakage Current	I <sub>GSS</sub>			∓10	μA	$V_{GS} = \mp 8 \text{ V}, V_{DS} = 0 \text{ V}$	
Gate Cut-off Voltage	V <sub>GS(off)</sub>	-0.4		-1.1	V	$V_{DS} = -10 \text{ V}, I_{D} = -1 \text{ mA}$	
Forward Transfer Admittance *1	y <sub>fs</sub>	4.5			S	$V_{DS} = -5 \text{ V}, I_{D} = -2 \text{ A}$	
Drain to Source On-state Resistance *1	R <sub>DS(on)1</sub>		63	79	mΩ	$V_{GS} = -4.5 \text{ V}, I_D = -1.5 \text{ A}$	
	R <sub>DS(on)2</sub>		78	105	mΩ	$V_{GS} = -2.5 \text{ V}, I_D = -1.5 \text{ A}$	
	R <sub>DS(on)3</sub>		109	182	mΩ	$V_{GS} = -1.8 \text{ V}, I_D = -1.5 \text{ A}$	
Input Capacitance	C <sub>iss</sub>		473		pF	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V},$	
Output Capacitance	Coss		88		pF	f = 1.0 MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>		68		pF		
Turn-on Delay Time	t <sub>d (on)</sub>		11.5		ns	$I_D = -1.5 \text{ A}, V_{DD} = -10.0 \text{ V},$	
Rise Time	t <sub>r</sub>		4.0		ns	$V_{GS} = -4.0 \text{ V}, R_G = 6 \Omega$	
Turn-off Delay Time	t <sub>d (off)</sub>		37.5		ns		
Fall Time	t <sub>f</sub>		12.5		ns		
Total Gate Charge	$Q_G$		5.1		nC	$I_D = -3.0 \text{ A}$ , $V_{DD} = -16 \text{ V}$ ,	
Gate to Source Charge	Q <sub>GS</sub>		0.9		nC	$V_{GS} = -4.5 \text{ V}$	
Gate to Drain Charge	Q <sub>GD</sub>		1.5		nC		
Body Diode Forward Voltage *1	V <sub>F(S-D)</sub>			1.5	V	I <sub>F</sub> = 3.0 A, V <sub>GS</sub> = 0 V	

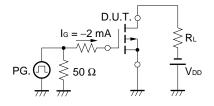
RENESAS

Note: \*1. Pulsed

### **TEST CIRCUIT 1 SWITCHING TIME**

# 

### **TEST CIRCUIT 2 GATE CHARGE**

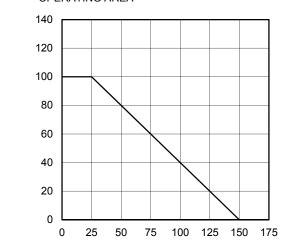


dT - Percentage of Rated Power - %

I<sub>D</sub> - Drain Current - A

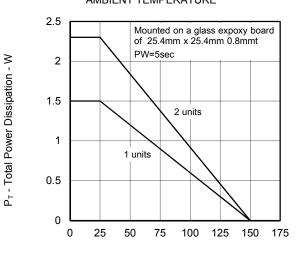
# Typical Characteristics ( $T_A = 25$ °C)

DERATING FACTOR OF FORWARD BIAS SAFE **OPERATING AREA** 



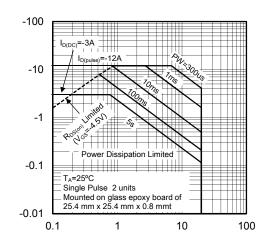
T<sub>A</sub> -Ambient Temperature - °C

### TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



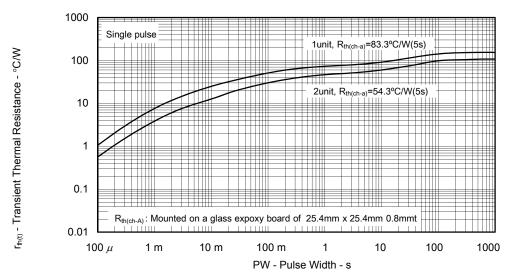
T<sub>A</sub> -Ambient Temperature - °C

### FORWARD BIAS SAFE OPERATING AREA



 $V_{\text{DS}}$  - Drain to Source Voltage - V

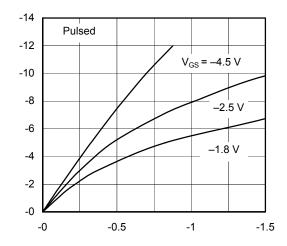
## TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



I<sub>D</sub> -Drain Current - A

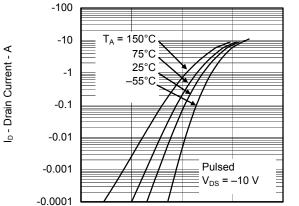
V<sub>GS(off)</sub> – Gate to Source Cut-off Voltage - V

# DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



V<sub>DS</sub> - Drain to Source Voltage - V

| y<sub>fs</sub> | - Forward Transfer Admittance - S



-0.5

-0

FORWARD TRANSFER CHARACTERISTICS

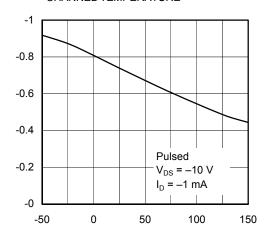
V<sub>GS</sub> - Gate to Source Voltage - V

-1

-1.5

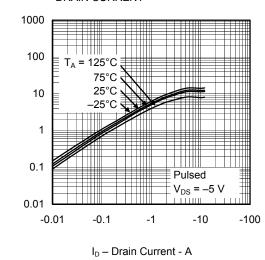
-2

# GATE TO SOURCE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE

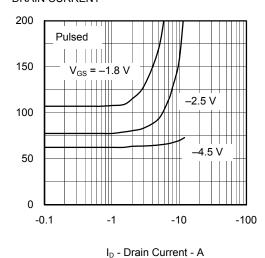


T<sub>ch</sub> - Channel Temperature - °C

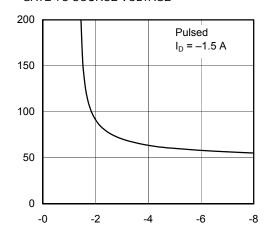
# FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



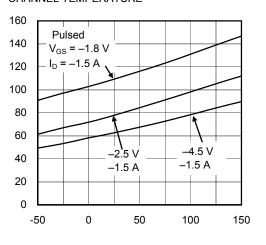
 $V_{\text{GS}}$  - Gate to Source Voltage - V

 $R_{\text{DS}(\text{on})}$  – Drain to Source On-state Resistance -  $m\Omega$ 

 $R_{\text{DS(on)}}$  - Drain to Source On-state Resistance -  $m\Omega$ 

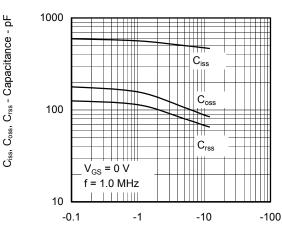
R<sub>DS(on)</sub> –Drain to Source On-state Resistance - mΩ

### DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



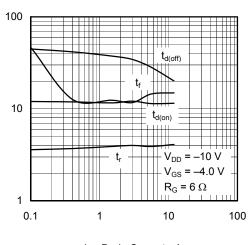
 $T_{\text{ch}}$  - Channel Temperature -  $^{\circ}C$ 

### CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



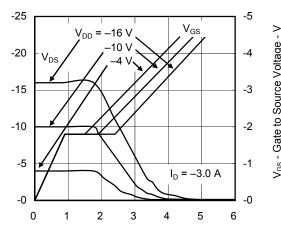
 $V_{\text{DS}}$  – Drain to Source Voltage - V

### SWITCHING CHARACTERISTICS



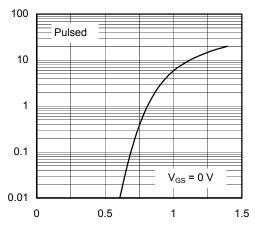
ID - Drain Current - A

#### DYNAMIC INPUT/OUTPUT CHARACTERISTICS



Q<sub>G</sub> - Gate Charge - nC

# SOURCE TO DRAIN DIODE FORWARD VOLTAGE



 $V_{F(S\!-\!D)}$  - Drain to Source Voltage - V

V<sub>DS</sub> - Drain to Source Voltage - V

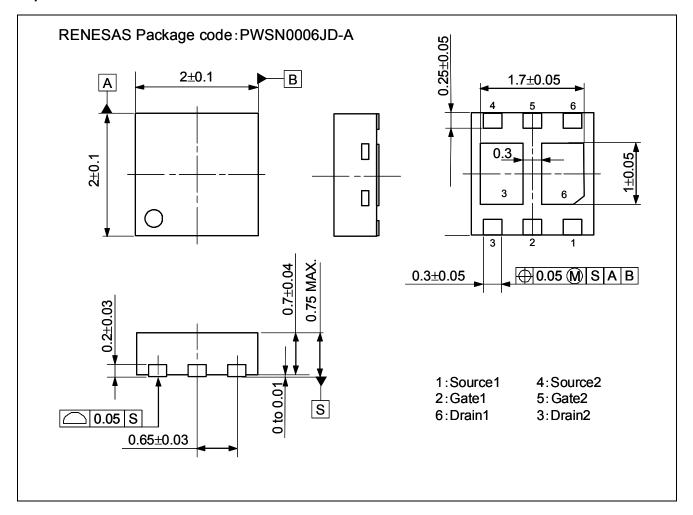
IF - Diode Forward Current - A

t<sub>d(on)</sub>, t<sub>f</sub>, t<sub>d(off)</sub>, t<sub>r</sub> - Switching Time - Ls

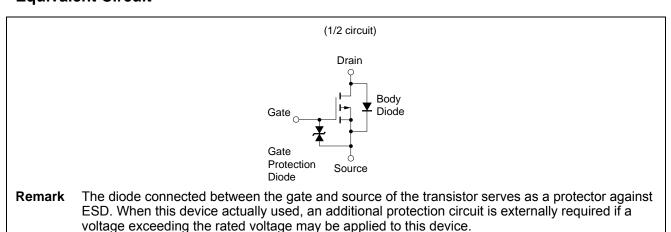
V<sub>GS</sub> - Gate to Source Voltage - V

## Package Drawings (Unit: mm)

### 6pinHUSON2020



# **Equivalent Circuit**



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